

REMARKS


Applicants acknowledge with appreciation the allowance of claims 46 and 47. Applicants also acknowledge the election of Group I, claims 1-36 and 46-47, for continued prosecution. This Amendment focuses on these elected claims. Claims 28, 34, and 35 are amended for reasons unrelated to patentability.

Claims 2, 8-14, 16, 18, 23-27, and 29-36 stand objected to as depending from a rejected claim. In view of the lack of any other rejection, Applicants understand this objection as indicating that these claims are considered allowable.

DrB *WGW 11/7/03*
Claims 1, 3, and 28 stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. patent 6,174,770 (Chi). Applicants respectfully traverse this rejection.

Claim 1 defines "A method of forming a catalyst body," and claim 28 defines "A method for forming a catalyst structure," each of which includes the performing of certain further recited acts. Chi does not disclose any method of forming a catalyst body or structure; in fact, the reference fails to mention catalysts at all. Chi is instead directed to the formation of a DRAM capacitor, which is unrelated to catalyst technology. That the capacitor of Chi may incorporate hemispherical grain polysilicon, which is oxidized, does not render the claim anticipated. Additionally, the oxidization of the HSG of Chi is not disclosed to necessarily result in a layer of silica.

Since Chi does not anticipate independent claims 1 or 28, these claims and dependent claim 3 are patentable over the reference. Applicants respectfully request that the 35 U.S.C. § 102(e) rejection of claims 1, 3, and 28 be withdrawn.



Claims 1, 3-7, 15, 17, 19-22, and 28 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Chi in view of U.S. patent 5,318,920 (Hayashide). Applicants respectfully traverse this rejection. The Hayashide reference has not been fully cited in the Office Action, nor has a copy of the reference been provided. However, based on the Applicants own investigation, the identity of the Hayashide reference has been assumed to be that of the patent indicated above and Applicants have acquired a copy of said reference independently of the U.S. Patent and Trademark Office.

Claims 1, 3, and 28 have been discussed above as being patentable over Chi alone. Hayashide, like Chi, is not directed to a method of forming a catalyst body or structure as claimed, but discloses the manufacture of a capacitor structure, which is unrelated to catalyst technology. Hayashide can add no teaching or suggestion to the disclosure of Chi so that the combined of references would have rendered the subject matter of the claims obvious. The references are directed to a technology wholly unrelated to the subject matter of the claims. Thus, independent claims 1 and 28, and depending claims 3-7, 15, 17, and 19-22 are patentable over the references, whether taken individually or in combination. Applicants respectfully request that the 35 U.S.C. § 103(a) rejection of these claims be withdrawn.

In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. According, the Examiner is respectfully requested to pass this application to issue.

Dated: September 12, 2003

Respectfully submitted,

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